

TOSHIBA

TC55V328BJ/BFT-12,-15

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

32,768-WORD BY 8-BIT CMOS STATIC RAM

DESCRIPTION

The TC55V328BJ/BFT is a 262,144-bit high-speed static random access memory (SRAM) organized as 32,768 words by 8 bits. Fabricated using CMOS technology and advanced circuit techniques to provide high speed and low-voltage operation, it operates from a single 3.3 V power supply. There are two control inputs. Chip enable (\overline{CE}) can be used to place the device in a low-power mode, and output enable (\overline{OE}) provides fast memory access. This device is well suited to cache memory applications where high-speed access and high-speed storage are required. All inputs and outputs are directly LVTTL compatible. The TC55V328BJ/BFT is available in plastic 28-pin SOJ (300 mil width) and TSOP packages for high density surface assembly.

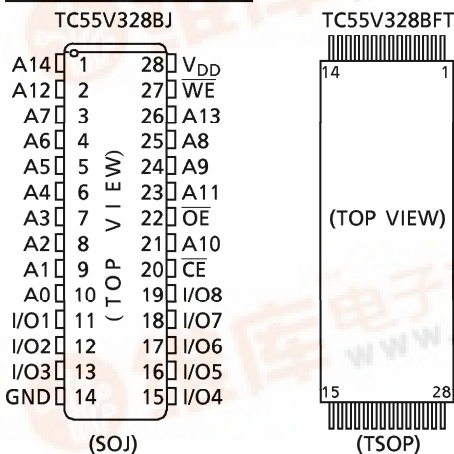
FEATURES

- Fast access time (the following are maximum values)
 - TC55V328BJ/BFT-12: 12 ns
 - TC55V328BJ/BFT-15: 15 ns
- Low-power dissipation (the following are maximum values)
 - Operating: 120 mA (12 ns type)
 - Operating: 100 mA (15 ns type)
 - Standby : 300 μ A (all devices)
- Single power supply voltage:
 - TC55V328BJ/BFT-12 : 3.3V + 0.3V or -0.2V
 - TC55V328BJ/BFT-15 : 3.3V \pm 0.3V
- Fully static operation
- All inputs and outputs are LVTTL compatible
- Output buffer control using OE
- Packages:
 - SOJ28-P-300-1.27A (BJ) (Weight: 0.83 g typ)
 - TSOP I 28-P-0.55 (BFT) (Weight: 0.22 g typ)

PIN ASSIGNMENT

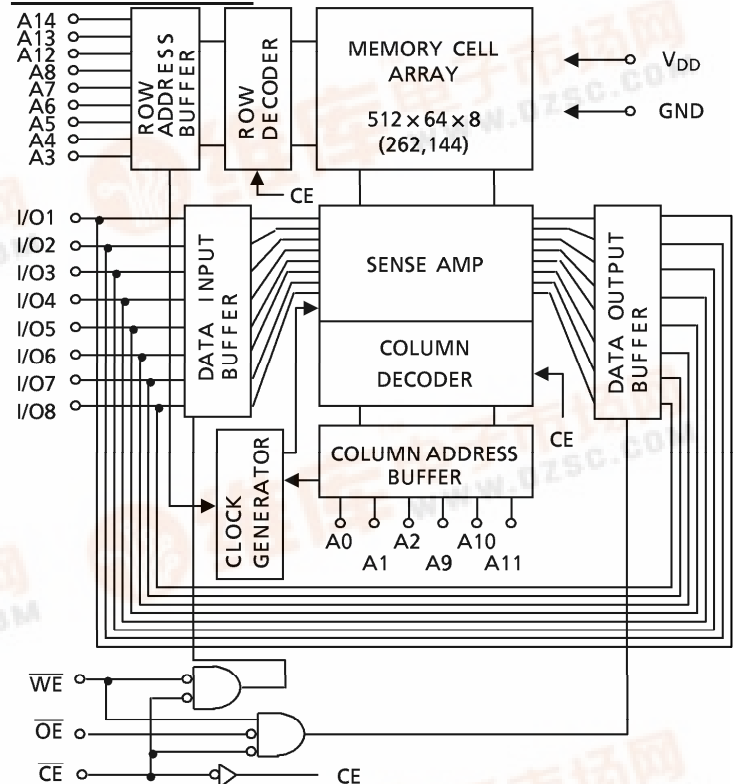
A0 to A14	Address Inputs
I/O1 to I/O8	Data Inputs / Outputs
\overline{CE}	Chip Enable Input
\overline{WE}	Write Enable Input
\overline{OE}	Output Enable Input
V_{DD}	Power (+ 3.3V)
GND	Ground

PIN CONNECTION



Pin No.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
Pin Name	\overline{OE}	A ₁₁	A ₉	A ₈	A ₁₃	\overline{WE}	V_{DD}	A ₁₄	A ₁₂	A ₇	A ₆	A ₅	A ₄	A ₃
Pin No.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
Pin Name	A ₂	A ₁	A ₀	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	\overline{CE}	A ₁₀

BLOCK DIAGRAM



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MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	- 0.5 to 4.6	V
V _{IN}	Input Voltage	- 0.5* to 4.6	V
V _{I/O}	Input/Output Voltage	- 0.5* to V _{DD} + 0.5**	V
P _D	Power Dissipation	0.5	W
T _{solder}	Soldering Temperature (10 s)	260	°C
T _{strg}	Storage Temperature	- 65 to 150	°C
T _{opr}	Operating Temperature	- 10 to 85	°C

*: - 1.5V with a pulse width of 20% of t_{RC} (4ns max.)

**: V_{DD} + 1.5V with a pulse width of 20% of t_{RC} (4ns max.)

DC RECOMMENDED OPERATING CONDITIONS (Ta = 0° to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT	
V _{DD}	Power Supply Voltage	-12	3.1	3.3	3.6	V
		-15	3.0	3.3	3.6	
V _{IH}	Input High Voltage	2.0	-	V _{DD} + 0.3**	V	
V _{IL}	Input Low Voltage	- 0.3*	-	0.8	V	

* : - 1.0V with a pulse width of 20% of t_{RC} (4ns max.)

** : V_{DD} + 1.0V with a pulse width of 20% of t_{RC} (4ns max.)

DC CHARACTERISTICS (Ta = 0° to 70°C, -12:V_{DD} = 3.3V + 0.3V or -0.2V, -15:V_{DD} = 3.3V ± 0.3V)

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}	-	-	± 1	μA	
I _{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ V _{OUT} = 0 V to V _{DD}	-	-	± 1	μA	
V _{OH}	Output High Voltage	I _{OH} = - 2 mA	2.4	-	-	V	
		I _{OH} = - 100 μA	V _{DD} - 0.2	-	-		
V _{OL}	Output Low Voltage	I _{OL} = 2 mA	-	-	0.4	V	
		I _{OL} = 100 μA	-	-	0.2		
I _{DDO}	Operating Current	tcycle = Minimum Cycle, $\overline{CE} = V_{IL}$ Other Inputs = V _{IH} or V _{IL} , I _{out} = 0 mA	- 12	-	-	120	mA
			- 15	-	-	100	
I _{DDS1}	Standby Current	$\overline{CE} = V_{IH}$ Other Inputs = V _{IH} or V _{IL} , tcycle = Minimum Cycle	-	-	20	mA	
I _{DDS2}		$\overline{CE} = V_{DD} - 0.2 V$ Other Inputs = V _{DD} - 0.2 V or 0.2 V	-	-	300	μA	

CAPACITANCE (Ta = 25°C, f = 1.0 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	6	pF
C _{I/O}	Input/Output Capacitance	V _{I/O} = GND	10	pF

Note: This parameter is periodically sampled and is not 100% tested.

OPERATING MODE

MODE	\overline{CE}	\overline{OE}	\overline{WE}	I/O1 to I/O8	POWER
Read	L	L	H	Output	I _{DDO}
Write	L	x	L	Input	I _{DDO}
Outputs Disable	L	H	H	High Impedance	I _{DDO}
Standby	H	x	x	High Impedance	I _{DDs}

x: Don't care

AC CHARACTERISTICS ($T_a = 0^\circ$ to 70°C , -12: $V_{DD} = 3.3\text{V} + 0.3\text{V}$ or -0.2V , -15: $V_{DD} = 3.3\text{V} \pm 0.3\text{V}$)

READ CYCLE

SYMBOL	PARAMETER	TC55 V328BJ/BFT-12		TC55 V328BJ/BFT-15		UNIT
		MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	12	-	15	-	ns
t_{ACC}	Address Access Time	-	12	-	15	
t_{CO}	Chip Enable Access Time	-	12	-	15	
t_{OE}	Output Enable Access Time	-	6	-	7	
t_{OH}	Output Data Hold Time from Address Change	3	-	3	-	
t_{COE}	Output Enable Time from Chip Enable	3	-	3	-	
t_{COD}	Output Disable Time from Chip Enable	-	7	-	8	
t_{OEE}	Output Enable Time from Output Enable	1	-	1	-	
t_{ODO}	Output Disable Time from Output Enable	-	7	-	8	

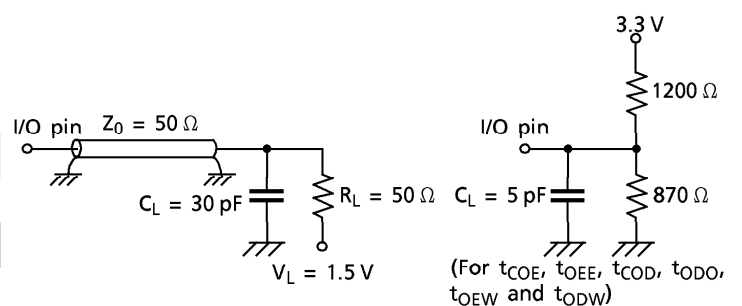
WRITE CYCLE

SYMBOL	PARAMETER	TC55 V328BJ/BFT-12		TC55 V328BJ/BFT-15		UNIT
		MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	12	-	15	-	ns
t_{WP}	Write Pulse Width	8	-	10	-	
t_{AW}	Address Valid to End of Write	10	-	10	-	
t_{CW}	Chip Enable to End of Write	10	-	11	-	
t_{AS}	Address Setup Time	0	-	0	-	
t_{WR}	Write Recovery Time	0	-	0	-	
t_{DS}	Data Setup Time	7	-	8	-	
t_{DH}	Data Hold Time	0	-	0	-	
t_{OEW}	Output Enable Time from \overline{WE}	1	-	1	-	
t_{ODW}	Output Disable Time from \overline{WE}	-	7	-	8	

AC TEST CONDITIONS

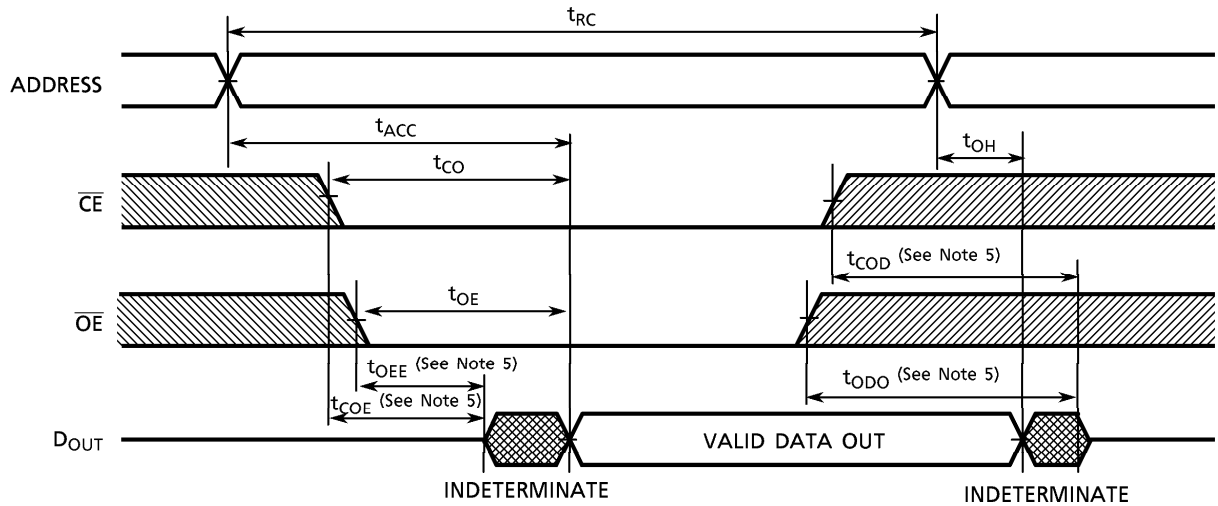
Input Pulse Levels	3.0 V, 0.0 V
Input Pulse Rise and Fall Time	3 ns
Input Timing Measurement Reference Levels	1.5 V
Output Timing Measurement Reference Levels	1.5 V
Output Load	Fig. 1

FIG. 1

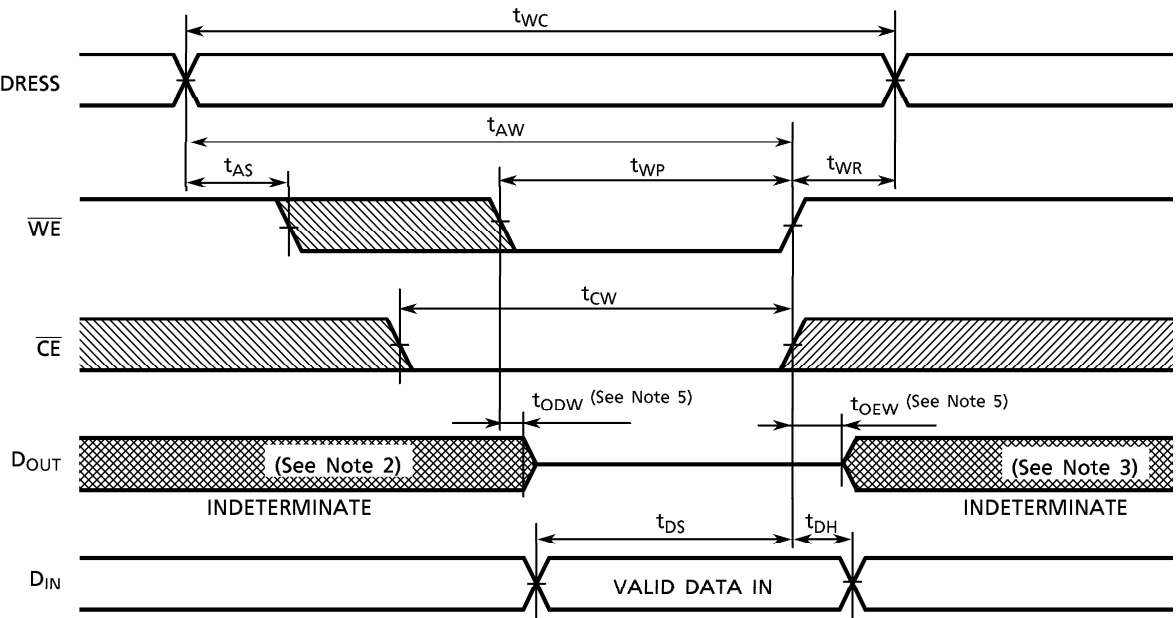


TIMING DIAGRAMS

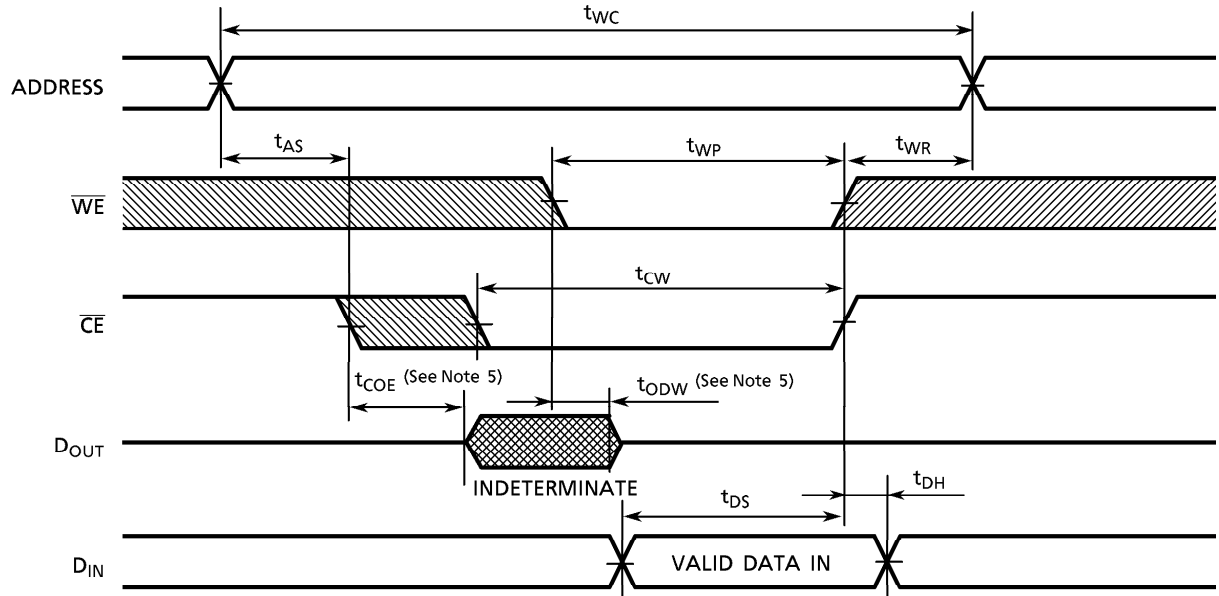
READ CYCLE (See Note 1)



WRITE CYCLE (\overline{WE} CONTROLLED 1) (See Note 4)



WRITE CYCLE 2 (\overline{CE} CONTROLLED) (See Note 4)



Note: (1) \overline{WE} remains HIGH for the read cycle.

(2) If \overline{CE} goes LOW coincident with or after \overline{WE} goes LOW, the outputs will remain at high impedance.

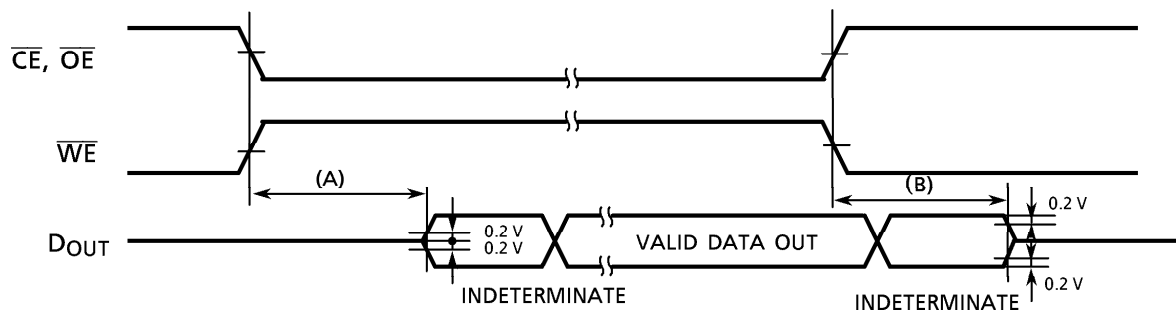
(3) If \overline{CE} goes HIGH coincident with or before \overline{WE} goes HIGH, the outputs will remain at high impedance.

(4) If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.

(5) The parameters are specified below measured using the load shown in Fig. 1.

(A) t_{COE} , t_{OEE} , $t_{OE\overline{W}}$ Output Enable Time

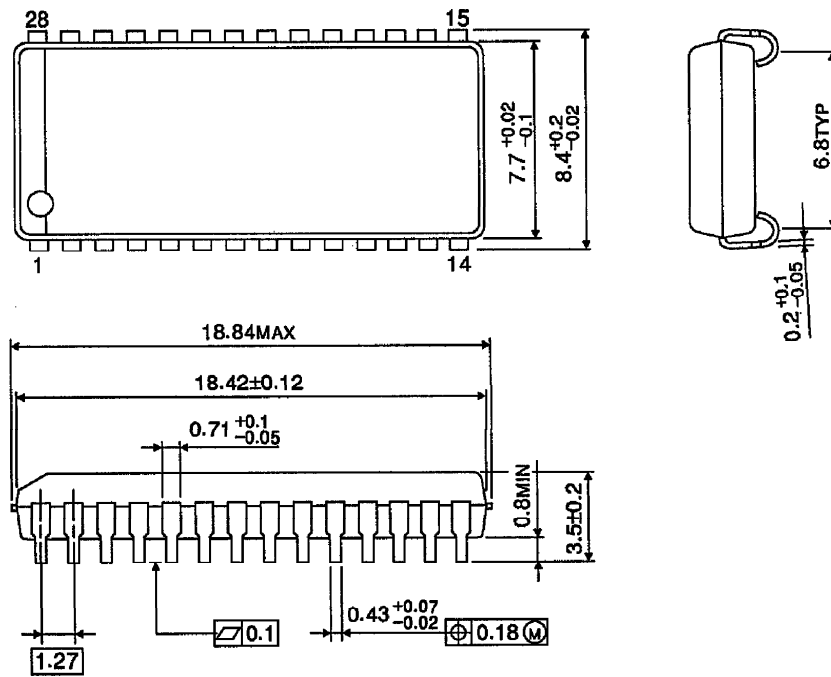
(B) t_{COD} , t_{ODO} , $t_{OD\overline{W}}$ Output Disable Time



OUTLINE DRAWINGS

Plastic SOJ (SOJ28-P-300-1.27A)

Unit in mm

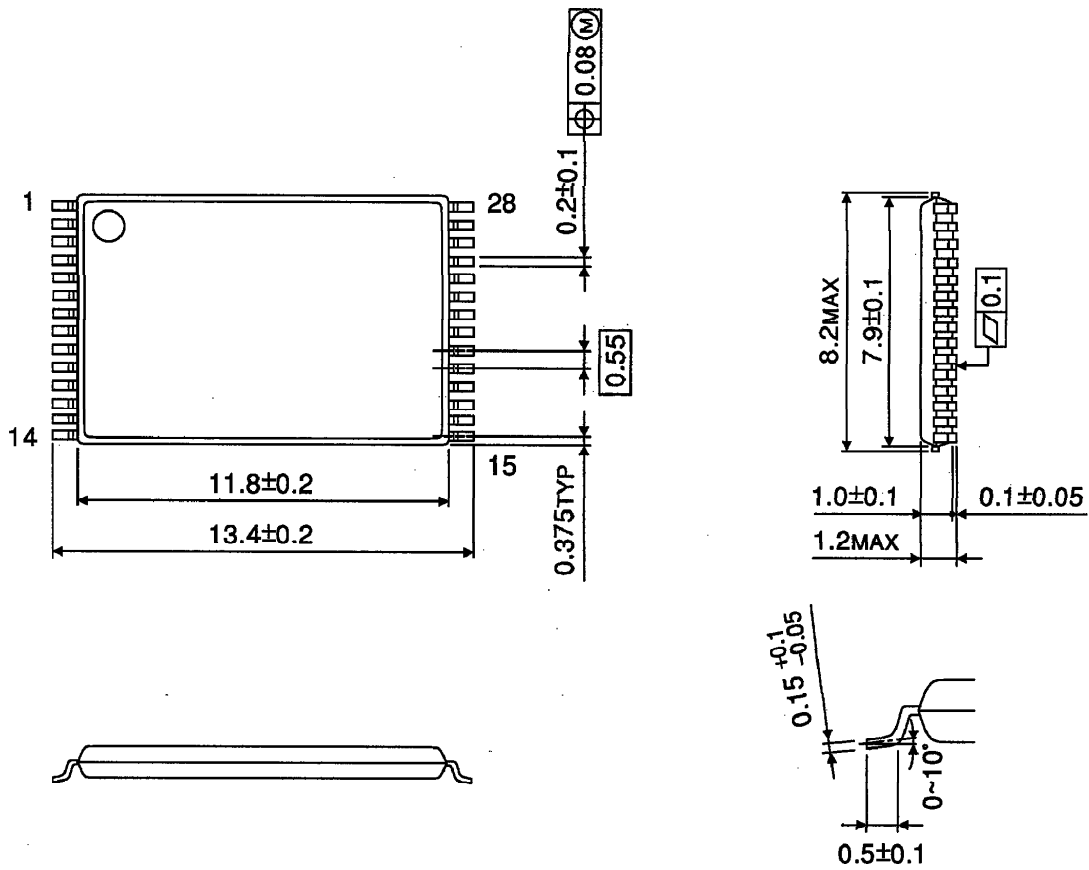


Weight : 0.83g (Typ.)

OUTLINE DRAWINGS

Plastic TSOP (TSOP I 28-P-0.55)

Unit in mm



Weight : 0.22g (Typ.)